

# PATENT ABSTRACTS OF JAPAN

(11)Publication number : 02-129913

(43)Date of publication of application : 18.05.1990

---

(51)Int.Cl.

H01L 21/205

---

(21)Application number : 63-282801

(71)Applicant : FUJITSU LTD

(22)Date of filing : 09.11.1988

(72)Inventor : MOCHIZUKI KOJI  
OZEKI MASASHI

---

## (54) MANUFACTURE OF SEMICONDUCTOR DEVICE

### (57)Abstract:

PURPOSE: To enable adsorption formation of excess-free Ga atomic layer by restraining taking-in of C atom which becomes impurity by adsorbing Ga atom mainly through TEG and by adsorbing lacking Ga atoms through TMG.

CONSTITUTION: When a Ga atomic layer is adsorbed to an atomic plane of a substrate, a Ga atom amount which does not cause Ga adsorption in excess of one atomic layer is adsorbed at first using triethylgallium (TEG) as a raw material. Then, lacking Ga atoms are adsorbed to one atomic layer at Ga atomic layer to complete a Ga layer of one atomic layer using trimethylgallium(TMg) as a raw material. Arsine is used as a raw material of As in the growth of GaAs, and As which is another element to constitute compound semiconductor is supplied. Adsorption formation of excess-free Ga atomic layer can be realized in this way.

---

## LEGAL STATUS

[Date of request for examination]

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]

[Date of registration]

[Number of appeal against examiner's decision of rejection]

[Date of requesting appeal against examiner's decision of rejection]

[Date of extinction of right]